



SGM8042

670nA, Rail-to-Rail I/O Operational Amplifier

PRODUCT DESCRIPTION

The SGM8042 is guaranteed to operate with a single supply voltage as low as 1.4V, while drawing less than 670nA (TYP) of quiescent current per amplifier. This device is also designed to support rail-to-rail input and output operation. This combination of features supports battery-powered and portable applications.

The SGM8042 has a gain bandwidth product of 14.5kHz (TYP) and is unity gain stable. These specifications make this operational amplifier appropriate for low frequency applications, such as battery current monitoring and sensor conditioning.

The SGM8042 is offered in dual configuration. It is specified for the extended industrial (-40°C to +85°C) temperature range. The SGM8042 is available in the Green SOP8 and MSOP8 packages.

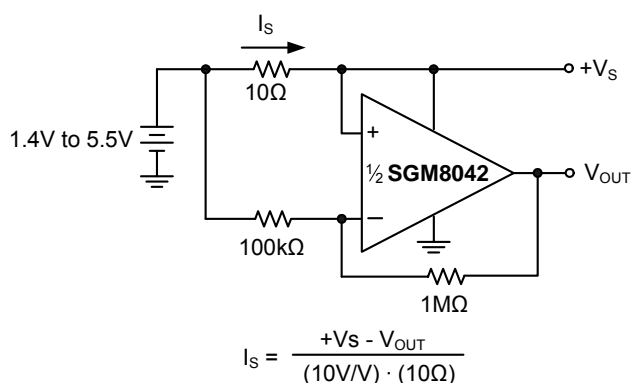
FEATURES

- **Low Quiescent Current:** 670nA/Amplifier (TYP)
- **Rail-to-Rail Input and Output**
- **Gain Bandwidth Product:** 14.5kHz at $V_S = 5V$ (TYP)
- **Wide Supply Voltage Range:** 1.4V to 5.5V
- **Unity Gain Stable**
- **-40°C to +85°C Operating Temperature Range**
- **Available in Green SOP8 and MSOP8 Packages**

APPLICATIONS

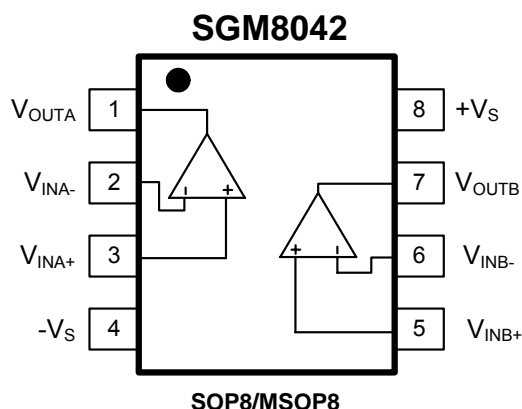
Toll Booth Tags
Wearable Products
Temperature Measurement
Battery Powered system

TYPICAL APPLICATION



High Side Battery Current Sensor

PIN CONFIGURATIONS (Top View)



PACKAGE/ORDERING INFORMATION

MODEL	ORDER NUMBER	PACKAGE DESCRIPTION	PACKAGE OPTION	MARKING INFORMATION
SGM8042	SGM8042YS8G/TR	SOP8	Tape and Reel, 2500	SGM8042YS8
	SGM8042YMS8G/TR	MSOP8	Tape and Reel, 3000	SGM8042YMS8

ABSOLUTE MAXIMUM RATINGS

Supply Voltage 6V
Analog Inputs (V_{IN+} , V_{IN-}) $(-V_S) - 0.1V$ to $(+V_S) + 0.1V$
Differential Input Voltage $|(-V_S) - (+V_S)|$
Storage Temperature Range $-65^{\circ}C$ to $+150^{\circ}C$
Junction Temperature $150^{\circ}C$
Operating Temperature Range $-40^{\circ}C$ to $+85^{\circ}C$
Lead Temperature Range (Soldering 10 sec)
. $260^{\circ}C$
ESD Susceptibility
HBM 4000V
MM 400V

NOTE:

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

CAUTION

This integrated circuit can be damaged by ESD if you don't pay attention to ESD protection. SGMICRO recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

ELECTRICAL CHARACTERISTICS

$+V_S = +1.4V$ to $+5.0V$, $-V_S = GND$, $T_A = +25^\circ C$, $V_{CM} = +V_S / 2$, $V_{OUT} \approx +V_S / 2$ and $R_L = 1M\Omega$ to $+V_S / 2$ ⁽¹⁾, unless otherwise noted.

PARAMETER		CONDITIONS	MIN	TYP	MAX	UNITS
DC ELECTRICAL CHARACTERISTICS						
Input Offset Voltage (V _{OS})		V _{CM} = +V _S /2		0.4	2.5	mV
Input Offset Voltage Drift (ΔV _{OS} /ΔT)		V _{CM} = +V _S /2, -40°C ≤ T _A ≤ +85°C		2.5		μV/°C
Power Supply Rejection Ratio (PSRR)		+V _S = 1.4V to 5.5V		80		dB
Common-Mode Input Range (V _{CMR})			-Vs - 0.1		+Vs + 0.1	V
Common-Mode Rejection Ratio (CMRR)		+V _S = 5.0V, V _{CM} = -0.1V to 5.1V		84		dB
		+V _S = 5.0V, V _{CM} = 2.5V to 5.1V		83		dB
		+V _S = 5.0V, V _{CM} = -0.1V to 2.5V		78		dB
Large Signal Voltage Gain (A _{Vo})		+V _S = 1.4V, R _L = 50kΩ, V _{OUT} = +V _S - 0.1V		80		dB
		+V _S = 2.5V, R _L = 50kΩ, V _{OUT} = +V _S - 0.1V		88		
		+V _S = 5.0V, R _L = 50kΩ, V _{OUT} = +V _S - 0.1V		93		
Input Bias Current (I _B)				1		pA
Input Offset Current (I _{OS})				1		pA
Maximum Output Voltage Swing	V _{OH}	+V _S = 1.4V, R _L = 50kΩ		1.395		V
		+V _S = 2.5V, R _L = 50kΩ		2.497		
		+V _S = 5.0V, R _L = 50kΩ		4.997		
	V _{OL}	+V _S = 1.4V, R _L = 50kΩ		4.5		mV
		+V _S = 2.5V, R _L = 50kΩ		3.1		
		+V _S = 5.0V, R _L = 50kΩ		3.5		
Short Circuit Current (I _{SC})		+V _S = 2.5V		5.5		mA
		+V _S = 5.0V		24		
Supply Voltage			1.4		5.5	V
Quiescent Current / per Amplifier (I _Q)		+V _S = 1.4V		570		nA
		+V _S = 2.5V		620		
		+V _S = 5.0V		670	1500	

Specifications subject to changes without notice.

ELECTRICAL CHARACTERISTICS

$+V_S = +1.4V$ to $+5.0V$, $-V_S = GND$, $T_A = +25^\circ C$, $V_{CM} = +V_S / 2$, $V_{OUT} \approx +V_S / 2$ and $R_L = 1M\Omega$ to $+V_S / 2$, $C_L = 60pF$ ⁽¹⁾, unless otherwise noted.

PARAMETER	CONDITIONS	MIN	TYP	MAX	UNITS
AC ELECTRICAL CHARACTERISTICS					
Gain-Bandwidth Product (GBP)	$+V_S = 1.4V$		12		kHz
	$+V_S = 2.5V$		13.5		
	$+V_S = 5.0V$		14.5		
Slew Rate (SR)	$+V_S = 1.4V$, $V_{OUT} = 1V$ Step		3.8		V/ms
	$+V_S = 2.5V$, $V_{OUT} = 1V$ Step		4.0		
	$+V_S = 5.0V$, $V_{OUT} = 2V$ Step		4.2		
Phase Margin (PM)	$+V_S = 1.4V$ to $5.5V$		60		°
Input Voltage Noise (e_n p-p)	$+V_S = 1.4V$, $f = 0.1Hz$ to $10Hz$		3.7		μV_{p-p}
	$+V_S = 2.5V$, $f = 0.1Hz$ to $10Hz$		3.2		
	$+V_S = 5.0V$, $f = 0.1Hz$ to $10Hz$		3.2		
Input Voltage Noise Density (e_n)	$+V_S = 1.4V$, $f = 1kHz$		190		nV/\sqrt{Hz}
	$+V_S = 2.5V$, $f = 1kHz$		180		
	$+V_S = 5.0V$, $f = 1kHz$		180		

NOTE1: Refer to Figure 1 and Figure 2.

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TEST CIRCUITS

The test circuits used for the DC and AC tests are shown in Figure 1 and Figure 2. The bypass capacitors are laid out according to the rules discussed in “**Supply Bypass**”.

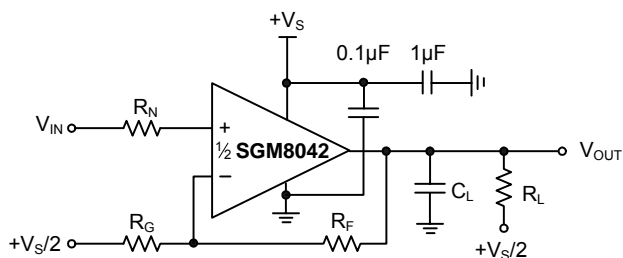


Figure 1. AC and DC Test Circuit for Most Non-Inverting Gain Conditions.

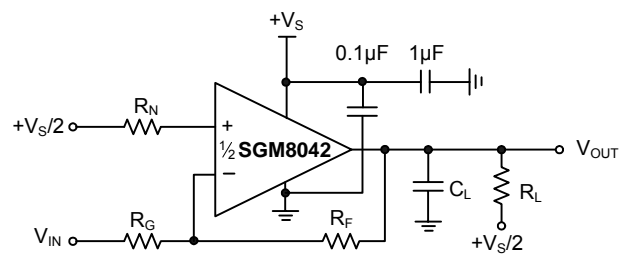
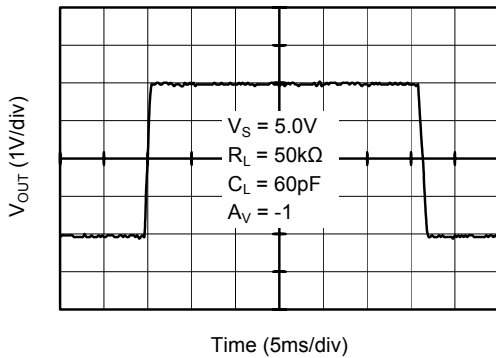


Figure 2. AC and DC Test Circuit for Most Inverting Gain Conditions.

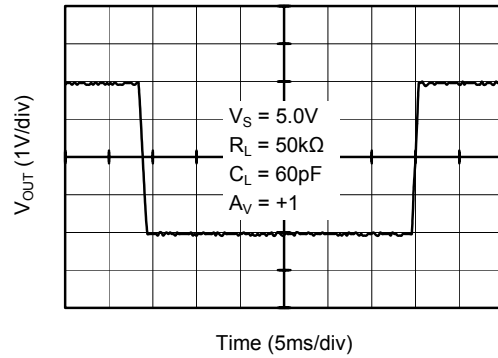
TYPICAL PERFORMANCE CHARACTERISTICS

$T_A = +25^\circ\text{C}$, $+V_S = +1.4\text{V}$ to $+5.0\text{V}$, $-V_S = \text{GND}$, $V_{CM} = +V_S / 2$, $V_{OUT} \approx +V_S / 2$ and $R_L = 1\text{M}\Omega$ to $+V_S / 2$, $C_L = 60\text{pF}$, unless otherwise noted.

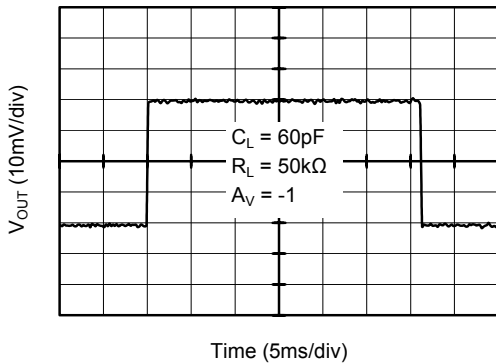
Large Signal Inverting Pulse Response



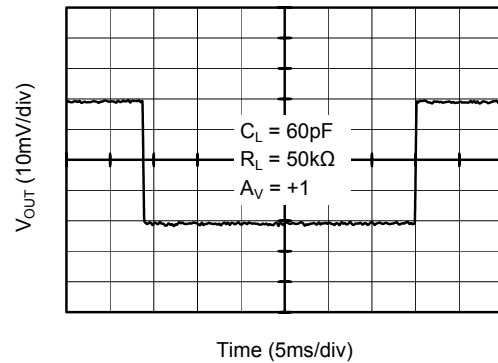
Large Signal Non-Inverting Pulse Response



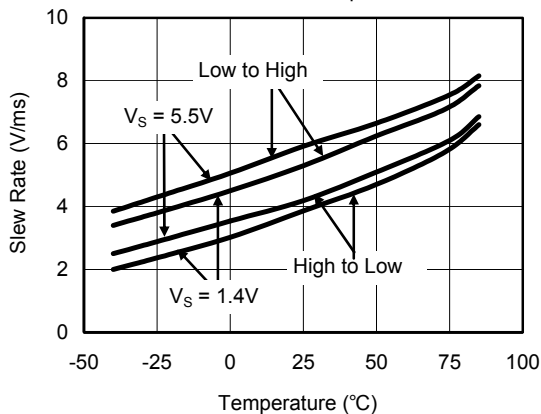
Small Signal Inverting Pulse Response



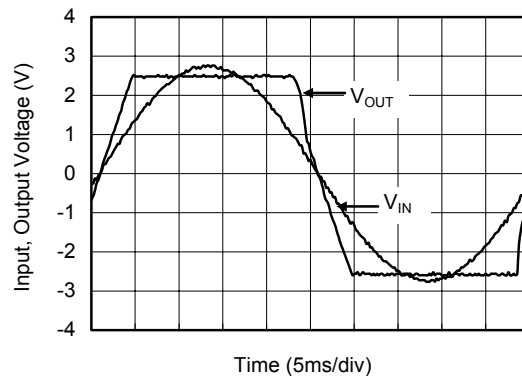
Small Signal Non-Inverting Pulse Response



Slew Rate vs. Temperature

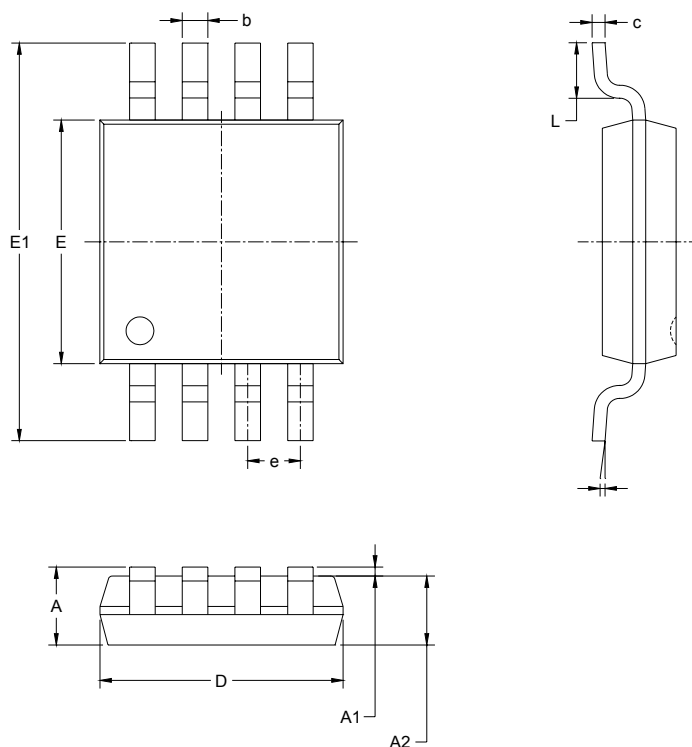


No Phase Reversal



PACKAGE OUTLINE DIMENSIONS

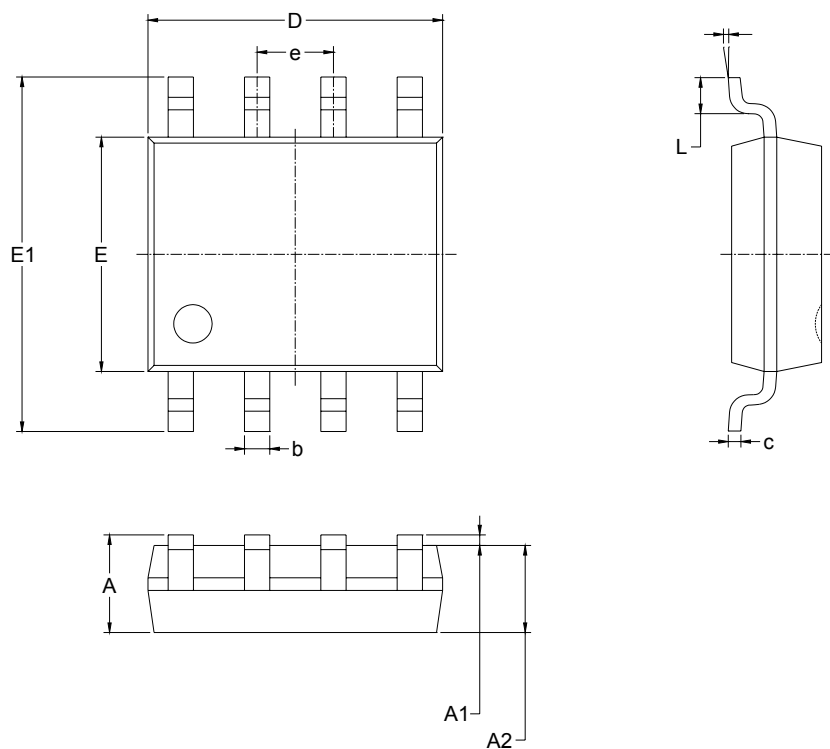
MSOP8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.820	1.100	0.032	0.043
A1	0.020	0.150	0.001	0.006
A2	0.750	0.950	0.030	0.037
b	0.250	0.380	0.010	0.015
c	0.090	0.230	0.004	0.009
D	2.900	3.100	0.114	0.122
e	0.650 BSC		0.026 BSC	
E	2.900	3.100	0.114	0.122
E1	4.750	5.050	0.187	0.199
L	0.400	0.800	0.016	0.031
θ	0°	6°	0°	6°

PACKAGE OUTLINE DIMENSIONS

SOP8



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.069
A1	0.100	0.250	0.004	0.010
A2	1.350	1.550	0.053	0.061
b	0.330	0.510	0.013	0.020
c	0.170	0.250	0.006	0.010
D	4.700	5.100	0.185	0.200
E	3.800	4.000	0.150	0.157
E1	5.800	6.200	0.228	0.244
e	1.270 BSC		0.050 BSC	
L	0.400	1.270	0.016	0.050
θ	0°	8°	0°	8°

SGMICRO is dedicated to provide high quality and high performance analog IC products to customers. All SGMICRO products meet the highest industry standards with strict and comprehensive test and quality control systems to achieve world-class consistency and reliability.

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